

SOT23 NPN SILICON PLANAR HIGH PERFORMANCE TRANSISTOR

FMMT451

ISSUE 3 - OCTOBER 1995

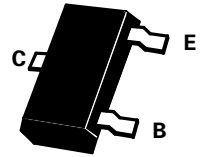


FEATURES

- * Low equivalent on-resistance; $R_{CE(sat)} 400m\Omega$ at 1A
- * 1 Amp continuous current
- * $P_{tot} = 500$ mW

COMPLEMENTARY TYPE – FMMT551

PARTMARKING DETAIL – 451



ABSOLUTE MAXIMUM RATINGS.

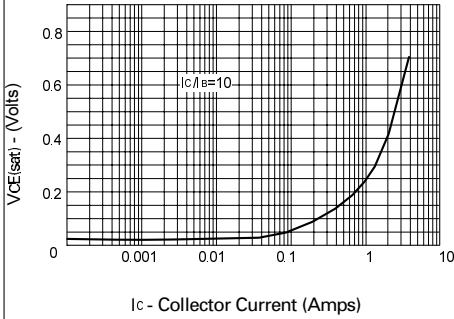
PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	2	A
Continuous Collector Current	I_C	1	A
Base Current	I_B	200	mA
Power Dissipation at $T_{amb}=25^\circ C$	P_{tot}	500	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$).

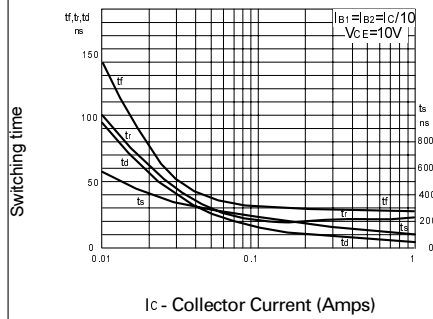
PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	80		V	$I_C = 100\mu A$
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	60		V	$I_C = 10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5		V	$I_E = 100\mu A$
Collector Cut-Off Current	I_{CBO}		0.1	μA	$V_{CB} = 60V$
Emitter Cut-Off Current	I_{EBO}		0.1	μA	$V_{EB} = 4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.35	V	$I_C = 150mA, I_B = 15mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.1	V	$I_C = 150mA, I_B = 15mA^*$
Static Forward Current Transfer Ratio	h_{FE}	50 10	150		$I_C = 150mA, V_{CE} = 10V^*$ $I_C = 1A, V_{CE} = 10V^*$
Transition Frequency	f_T	150		MHz	$I_C = 50mA, V_{CE} = 10V$ $f = 100MHz$
Output Capacitance	C_{obo}		15	pF	$V_{CB} = 10V, f = 1MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

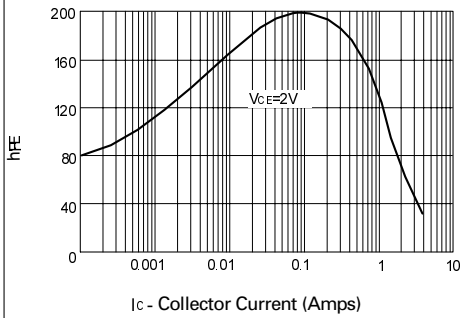
TYPICAL CHARACTERISTICS



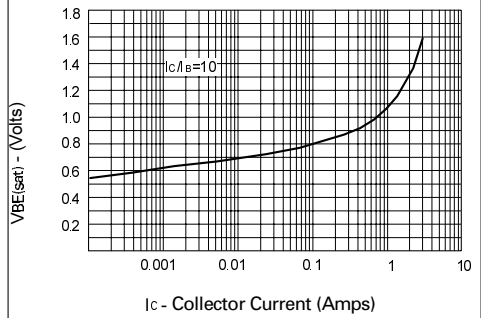
$V_{CE(sat)}$ v I_C



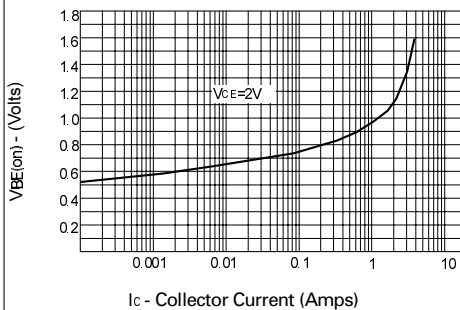
Switching Speeds



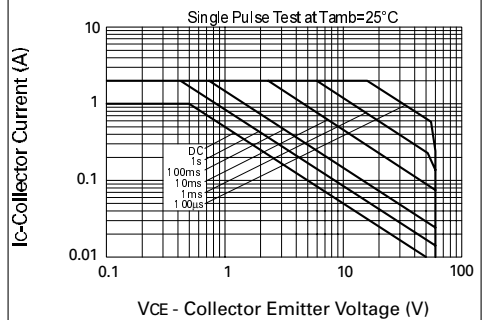
hFE v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area